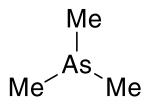


Catalog # 98-1975 Trimethylarsine, elec. gr. (99.995%-As) PURATREM



Thermal Behavior:

- Melting point: -87.3°C
- Boiling point: 56°C

Technical Notes:

1. CVD precursor for arsenic thin film deposition

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
GaAs	CVD	RT	60 Torr	GaMe ₃ , H ₂	450-600°C	1
InGaAs	CVD	RT	200 Torr	InMe ₃ , GaMe ₃ , H ₂	580-630°C	2

References:

1. [J. Cryst. Growth 1995, 147, 256](#)
2. [J. Cryst. Growth 1999, 197, 755](#)